PHOTOCOUPLERS **PS9601, PS9601L**

HIGH ISOLATION VOLTAGE HIGH SPEED PHOTOCOUPLER

PS9601, PS9601L are optically coupled isolators containing a GaAlAs LED on light emitting side (input side) and a photodiode and a signal processing circuit on light receiving side (output side) on one chip.

PS9601 is in a plastic DIP (Dual In-line Package) and PS9601L is lead bending type (Gull-wing) for surface mount.

FEATURES

NEC

- High isolation voltage BV: 5 000 Vr.m.s. MIN.
- High Propagation delay time tPHL, tPLH: 50 ns TYP.
- Low input current IFHL: 2.5 mA TYP.
- · Can be soldered by infrared reflow soldering
- Taping product number PS9601L-E3, E4
- UL recognized File No. E72422 (S)

APPLICATIONS

- · Computer and peripheral memory
- Electronic instrument
- Audio-visual

PACKAGE DIMENSIONS (Unit: mm)



ABSOLUTE MAXIMUM RATINGS (T_A = 25 $^{\circ}$ C)

| Diode | | | |
|-----------------------|------|-------------|---------|
| Forward Current | lf | 30 | mA |
| Reverse Voltage | VR | 5 | V |
| Power Dissipation | PD | 60 | mW |
| Detector | | | |
| Supply Voltage | Vcc | 7 | V |
| Output Voltage | Vo | 7 | V |
| Output Current | lo | 50 | mA |
| Enable Voltage | Ve | 5.5 | V |
| Power Dissipation | Pc | 85 | mW |
| Isolation Voltage *1 | BV | 5 000 | Vr.m.s. |
| Operating Temperature | Topt | -40 to +85 | °C |
| Storage Temperature | Tstg | -55 to +125 | °C |
| | | | |

*1 AC voltage for 1 minute $T_A = 25$ °C, RH = 60 % between input and output.

RECOMMENDED OPERATING CONDITIONS (TA = 25 °C)

| PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNIT |
|---------------------------|--------|------|------|------|------|
| Low Level Input Current | IFL | 0 | | 250 | μA |
| High Level Input Current | Ігн | 7 | 10 | 15 | mA |
| High Level Enable Voltage | Veh | 2 | | Vcc | V |
| High Level Enable Voltage | Vel | 0 | | 0.8 | V |
| Supply Voltage | Vcc | 4.5 | 5 | 5.5 | V |
| Operating Temperature | Topt | 0 | 25 | 70 | °C |

* By-pass capacitor of more than 0.1 μ F is used between Vcc and GND near device.

ELECTRICAL CHARACTERISTICS ($T_A = -40$ to +85 °C)

| Diode | PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNIT | TEST CONDITIONS | |
|----------|---------------------------|--------|------|------|------|------|--|--|
| | Forward Voltage | VF | 1.4 | 1.65 | 1.9 | V | IF = 10 mA, TA = 25 °C | |
| | Reverse Current | IR | | | 10 | μΑ | V _R = 5 V, T _A = 25 °C | |
| | Capacitance | Ct | | 60 | | pF | V = 0, f = 1 MHz, T _A = 25 °C | |
| Detector | High Level Output Current | Іон | | 2 | 250 | μΑ | Vcc = Vo = 5.5 V, IF = 250 μ s, Ve = 2 V | |
| | Low Level Output Voltage | Vol | | 0.2 | 0.6 | V | V_{CC} = 5.5 V, I_F = 5 mA, V_E = 2 V, I_O = 13 mA | |
| | High Level Supply Current | Іссн | 5 | 7 | 10 | mA | V_{CC} = 5.5 V, V_{E} = 0.5 V, I_{F} = 0 | |
| | Low Level Supply Current | IccL | 10 | 13 | 18 | mA | $V_{CC} = 5.5 \text{ V}, \text{ V}_{E} = 2 \text{ V}, \text{ I}_{F} = 10 \text{ mA}$ | |
| | High Level Enable Current | Іен | -0.7 | -1 | -1.5 | mA | Vcc = 5.5 V, VEH = 2 V | |
| | Low Level Enable Current | IEL | -1 | -1.4 | -2 | mA | $V_{CC} = 5.5 \text{ V}, \text{ Vel} = 0.5 \text{ V}$ | |

ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

| | PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNIT | TEST CONDITIONS |
|---------|--|--------|------------------|------|------|------|--|
| | Treshold Input Current High \rightarrow Low | Ifhl | 0.5 | 2.5 | 5 | mA | $V_{CC} = 5 \text{ V}, \text{ V}_{E} = 2 \text{ V}, \text{ T}_{A} = -40 \text{ to } + 85 ^{\circ}\text{C}$ $V_{O} = 0.8 \text{ V}, \text{ R}_{L} = 350 \Omega$ |
| | Isolation Resistance | R1-2 | 10 ¹¹ | | | Ω | $V_{in-out} = 1 \text{ kV}_{DC}$, RH 40 to 60 % |
| | Isolation Capacitance | C1-2 | | 0.6 | | pF | V = 0, f = 1 MHz |
| | Propagation Delay Time ^{*2} High \rightarrow Low | tрнL | | 50 | 75 | ns | $\label{eq:Vcc} \begin{array}{l} V_{CC} = 5 \ V, \ I_F = 7.5 \ mA \\ R_L = 350 \ \Omega, \ C_L = 15 \ pF \end{array}$ |
| Coupled | Propagation Delay Time* ² Low \rightarrow High | tр∟н | | 50 | 75 | ns | |
| | Rise Time | tr | | 20 | | ns | |
| | Fall Time | tr | | 10 | | ns | |
| | Enable Propagation Delay Time ^{*3} High → Low | tehl | | 10 | | ns | $\label{eq:Vcc} \begin{array}{l} V_{CC} = 5 \ V, \ I_F = 7.5 \ mA \\ V_{EH} = 3 \ V, \ V_{EL} = 0.5 \ V \\ R_L = 350 \ \Omega, \ C_L = 15 \ pF \end{array}$ |
| | Enable Propagation Delay Time ^{*3} Low \rightarrow High | telh | | 25 | | ns | |

*2 Test Circuit for Propagation delay time



* CL is approximately 15 pF, which includes probe and stray wiring capacitance.

*3 Test Circuit for enable Propagation delay time









PRECAUTIONS IN MOUNTING THE DEVICE

- (1) Precautions in mounting the device by infrared reflow soldering
 - Peak reflow temperature : 235 °C or below (Plastic surface temperature)
 - Reflow time : 30 seconds or less (Time period during which the plastic surface temperature • is 210 °C)
 - Number of reflow processes: One •
 - Flux •

: Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

INFRARED RAY REFLOW TEMPERATURE PROFILE



- (2) Precautions in mounting the device in solder dip method
 - Temperature
- : 260 °C or lower
- Time •
- Flux ٠

- : 10 sec. or less
- : Rosin group flux, where the amount of chloride component is small.

Caution

The Great Care must be taken in dealing with the devices in this guide. The reason is that the material of the devices is GaAs (Gallium Arsenide), which is designated as harmful substance according to the law concerned. Keep the law concerned and so on, especially in case of removal.

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Anti-radioactive design is not implemented in this product.

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